# Low Power, Rail-to-Rail Operational Amplifier

The NCV952 is a dual, low power, CMOS operational amplifier fully specified for 3 V and 5 V operation. Rail–to–rail output performance over the supply range of 2.7 V to 12 V provides increased dynamic range in single–supply and split–supply applications. This device offers a gain–bandwidth of 3.5 MHz and a slew rate of 1 V/ $\mu$ s, with only 0.7 mA of quiescent current. The NCV952 is available in a space saving 8–pin TSSOP8 package.

#### **Features**

- Rail-to-rail Input Common Mode Voltage Range
- Rail-to-rail Output Swing
- Wide Supply Range: 2.7 V to 12 V
- Excellent Gain-bandwidth and Speed: 3.5 MHz at 1 V/μs with 3 V Supply
- Low Quiescent Current: 0.7 mA at  $V_S = 3$  V per Channel
- PSRR: 105 dB Typical
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–free, Halogen Free/BFR Free and are RoHS Compliant

#### **Typical Applications**

- General Purpose Operational Amplifier
- Active Filters
- Signal Conditioning Amplifiers/ADC Buffers
- Set-top Boxes
- Laptop/Notebook Computers
- Transformer/Line Drivers
- Personal Entertainment Systems
- Cell Phones and Other Portable Communications
- Portable Headphone Speaker Drivers
- Instrumentation and Sensoring



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TSSOP-8 CASE 948S

#### **MARKING DIAGRAM**

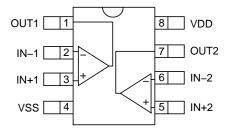


V52 = Specific Device Code

A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

#### **PIN CONNECTIONS**



#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NCV952DTBR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**Table 1. PIN DESCRIPTION** 

Pin	Name	Туре	Description
1	OUT1	Output	Output of opamp 1
2	IN-1	Input	Inverting input of opamp 1
3	IN+1	Input	Non-inverting input of opamp 1
4	VSS	Power	Negative supply. A bypass capacitor of 0.1 $\mu\text{F}$ to ground is recommended as close as possible to this pin.
5	IN+2	Input	Non-inverting input of opamp 2
6	IN-2	Input	Inverting input of opamp 2
7	OUT2	Output	Output of opamp 2
8	VDD	Power	Positive supply. A bypass capacitor of 0.1 $\mu F$ to ground is recommended as close as possible to this pin.

#### Table 2. ABSOLUTE MAXIMUM RATINGS (Over operating free-air temperature, unless otherwise stated)

Parameter	Symbol	Limit	Unit
Supply Voltage (V <sub>DD</sub> - V <sub>SS</sub> )	Vs	14	V
INPUT AND OUTPUT PINS			
Input Voltage	V <sub>IN</sub>	V <sub>SS</sub> – 0.3 to V <sub>DD</sub> + 0.3	V
Differential Input Voltage (Note 1)	V <sub>ID</sub>	±1	V
TEMPERATURE			
Storage Temperature	T <sub>STG</sub>	-65 to +150	°C
Junction Temperature	T <sub>J</sub>	+150	°C
ESD RATINGS (Note 2)			
Human Body Model	HBM	2500	V
Machine Model	MM	300	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### Table 3. THERMAL INFORMATION (Note 3)

Parameter	Symbol	Value	Unit
i di dilietei	Symbol	value	Offic
Junction to Ambient (Note 4)	$\theta_{\sf JA}$	140	°C/W
Junction to Case Top (Note 4)	ΨЈТ	34	°C/W

<sup>3.</sup> Short-circuits can cause excessive heating and destructive dissipation. Values are typical.

#### **Table 4. RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	Limit	Unit
Operating Supply Voltage	V <sub>S</sub>	2.7 to 12	V
Specified Operating Range	T <sub>A</sub>	-40 to +125	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

<sup>1.</sup> Input differential voltage is the non–inverting pin with respect to the inverting pin. If V<sub>ID</sub> > ±1 V, the maximum input current must not exceed ±1 mA; an input series resistor must be used to limit the input current.

<sup>2.</sup> This device series incorporates ESD protection and is tested by the following methods:

ESD Human Body Model tested per AEC-Q100-002 (JEDEC standard: JESD22-A114)

ESD Machine Model tested per AEC-Q100-003 (JEDEC standard: JESD22-A115)

<sup>4.</sup> Multilayer board, 1 oz. copper, 400 mm<sup>2</sup> copper area, both junctions heated equally.

Table 5. ELECTRICAL CHARACTERISTICS AT  $V_S = 3.0 \text{ V}$ At  $T_A = +25^{\circ}\text{C}$ ,  $V_{CM} = V_{OUT} =$  midsupply, unless otherwise noted. Boldface limits apply over the specified temperature range,  $T_A = -40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ , guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS	•					
Offset Voltage	Vos			0.6		mV
					8	mV
Offset Voltage Drift	ΔV/ΔΤ			2		μV/°C
Input Bias Current	I <sub>IB</sub>			55	100	nA
					200	nA
Input Offset Current	los			1	30	nA
					80	nA
Input Common Mode Range	V <sub>CM</sub>		V <sub>SS</sub> - 0.2		V <sub>DD</sub> + 0.2	V
Common Mode Rejection Ratio	CMRR	$V_{SS} + 0.15 < V_{CM} < V_{DD} - 0.15$	50	80		dB
OUTPUT CHARACTERISTICS				-		
Output Voltage High	V <sub>OH</sub>	$R_L = 600 \Omega$	V <sub>DD</sub> – 0.2	V <sub>DD</sub> – 0.08		V
Output Voltage Low	V <sub>OL</sub>	$R_L = 600 \Omega$		V <sub>SS</sub> + 0.10	V <sub>SS</sub> + 0.25	V
Short Circuit Current	I <sub>SC</sub>		10			mA
NOISE PERFORMANCE						
Voltage Noise Density	e <sub>N</sub>	f = 1 kHz, no load		25		nV/√Hz
DYNAMIC PERFORMANCE						
Open Loop Voltage Gain	A <sub>VOL</sub>	$V_O = 2 \text{ Vpp}, R_L = 600 \Omega$		88		dB
Gain Bandwidth Product	GBWP	$R_L = 2 k\Omega$		3.5		MHz
Gain Margin	A <sub>M</sub>	$R_L = 600 \Omega$ , $C_L = 100 pF$		8		dB
Phase Margin	ψм	$R_L = 600 \Omega$ , $C_L = 100 pF$		56		٥
Slew Rate	SR			1		V/μS
Total Harmonic Distortion + Noise	THD+N	$V_{OUT} = 2 \text{ Vpp, } f_{IN} = 10 \text{ kHz,}$ $A_V = 2, R_L = 10 \text{ k}\Omega$		0.008		%
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	V <sub>S</sub> = 2.7 V to 3.3 V	60	105		dB
Quiescent Current	I <sub>DD</sub>	No load, V <sub>CM</sub> = V <sub>S</sub> /2, per channel		0.7	1.3	mA

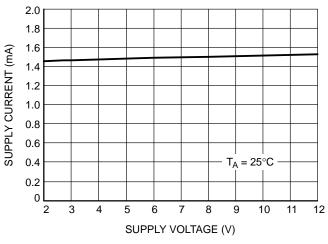
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 6. ELECTRICAL CHARACTERISTICS AT  $V_S = 5.0 \text{ V}$ At  $T_A = +25^{\circ}\text{C}$ ,  $V_{CM} = V_{OUT} =$  midsupply, unless otherwise noted. Boldface limits apply over the specified temperature range,  $T_A = -40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ , guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS	•		•	•	•	
Offset Voltage	Vos			0.6		mV
					8	mV
Offset Voltage Drift	ΔV/ΔΤ			2		μV/°C
Input Bias Current	I <sub>IB</sub>			55	100	nA
					200	nA
Input Offset Current	Ios			1	30	nA
					80	nA
Input Common Mode Range	V <sub>CM</sub>		V <sub>SS</sub> - 0.2		V <sub>DD</sub> +0.2	V
Common Mode Rejection Ratio	CMRR	$V_{SS} + 0.15 < V_{CM} < V_{DD} - 0.15$	50	85		dB
OUTPUT CHARACTERISTICS						
Output Voltage High	V <sub>OH</sub>	$R_L = 600 \Omega$	V <sub>DD</sub> -0.30	V <sub>DD</sub> -0.10		V
Output Voltage Low	V <sub>OL</sub>	$R_L = 600 \Omega$		V <sub>SS</sub> +0.14	V <sub>SS</sub> +0.30	V
Short Circuit Current	I <sub>SC</sub>		10			mA
NOISE PERFORMANCE						
Voltage Noise Density	e <sub>N</sub>	f = 1 kHz, no load		25		nV/√Hz
DYNAMIC PERFORMANCE						
Open Loop Voltage Gain	A <sub>VOL</sub>	$V_O = 2 \text{ Vpp}, R_L = 600 \Omega$		88		dB
Gain Bandwidth Product	GBWP	$R_L = 2 k\Omega$		3.6		MHz
Gain Margin	A <sub>M</sub>	$R_L = 600 \Omega, C_L = 100 pF$		9		dB
Phase Margin	ψм	$R_L = 600 \Omega, C_L = 100 pF$		60		0
Slew Rate	SR			1		V/μS
Total Harmonic Distortion + Noise	THD+N	$V_{OUT} = 4 \text{ Vpp, } f_{IN} = 10 \text{ kHz,}$ $A_V = 2, R_L = 10 \text{ k}\Omega$		0.008		%
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_S = 2.7 \text{ V to } 3.3 \text{ V}$	60	105		dB
Quiescent Current	I <sub>CC</sub>	No load, V <sub>CM</sub> = V <sub>S</sub> /2, per channel		0.75	1.4	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

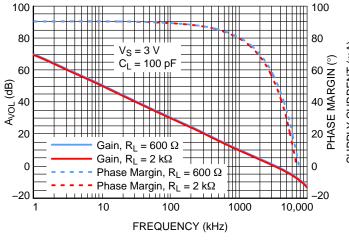
#### **TYPICAL CHARACTERISTICS**



40 SHORT CIRCUIT CURRENT (mA) 30 V<sub>S</sub> = 3 V, Sinking 20 10  $V_S = 5 V$ , Sinking 0 -10 V<sub>S</sub> = 3 V, Sourcing -20 V<sub>S</sub> = 5 V, Sourcing -30 0.5 2.0 2.5 3.0 3.5 4.0 0 1.0 1.5 4.5 5.0 **OUTPUT VOLTAGE (V)** 

Figure 1. Supply Current vs. Supply Voltage

Figure 2. Output Short Circuit Current vs.
Output Voltage



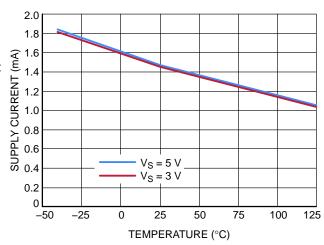
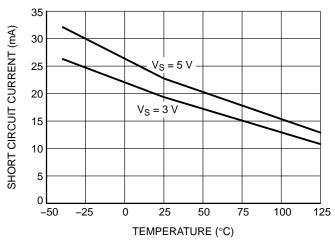


Figure 3. Open Loop Gain and Phase Margin vs. Frequency

Figure 4. Supply Current vs. Temperature



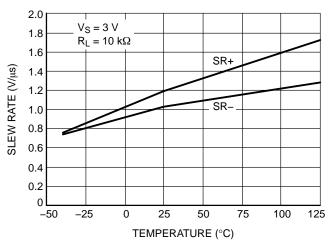


Figure 5. Output Short Circuit Current vs.Temperature

Figure 6. Slew Rate vs. Temperature

#### TYPICAL CHARACTERISTICS

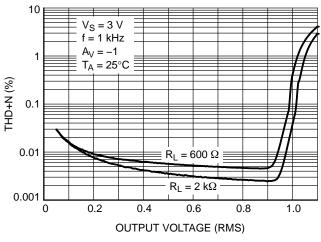


Figure 7. THD+N vs. Output Voltage

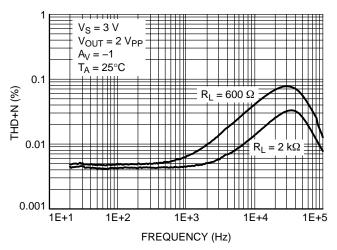


Figure 8. THD+N vs. Frequency

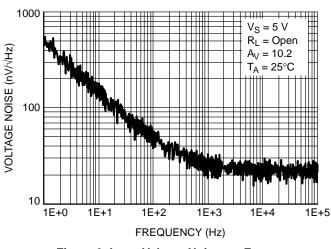


Figure 9. Input Voltage Noise vs. Frequency

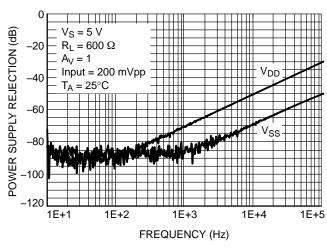


Figure 10. PSRR vs. Frequency

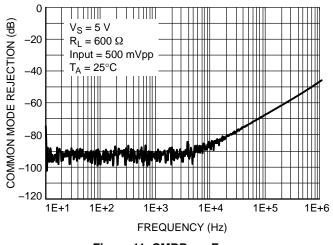


Figure 11. CMRR vs. Frequency

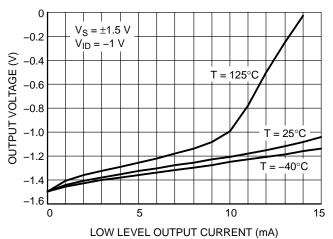


Figure 12. Low Level Output Voltage vs. **Output Current** 

#### **TYPICAL CHARACTERISTICS**

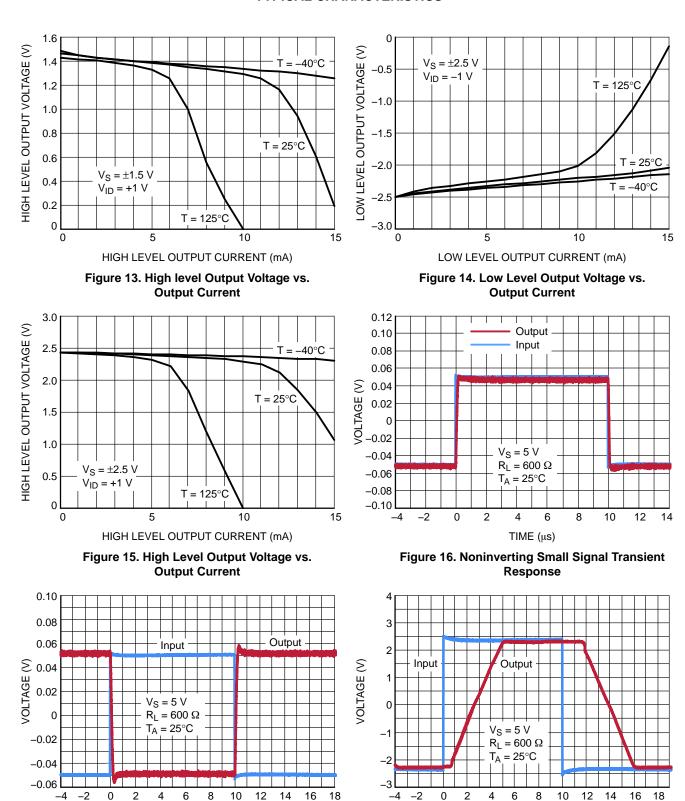


Figure 17. Inverting Small Signal Transient Response

TIME (µs)

Figure 18. Noninverting Large Signal Transient Response

TIME (µs)

## **TYPICAL CHARACTERISTICS**

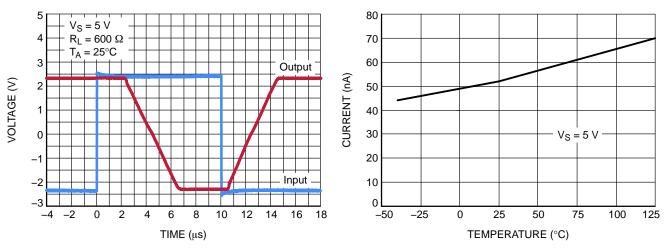


Figure 19. Inverting Large Signal Transient Response

Figure 20. Input Bias Current vs. Temperature

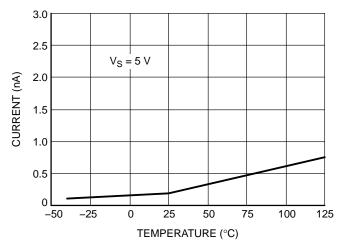
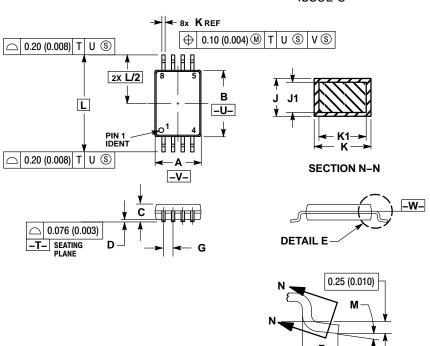


Figure 21. Input Offset Current vs. Temperature

#### PACKAGE DIMENSIONS

#### TSSOP-8 CASE 948S **ISSUE C**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD
- FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	2.90	3.10	0.114	0.122	
В	4.30	4.50	0.169	0.177	
С		1.10		0.043	
D	0.05	0.15	0.002	0.006	
F	0.50	0.70	0.020	0.028	
G	0.65 BSC		0.026 BSC		
J	0.09 0.20		0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252		
М	0°	8°	0°	8°	

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